

ABSTRACT OF THE DISCLOSURE

The present invention is a method for producing a single crystal by Czochralski method with pulling the single crystal from raw material melt in a crucible heated and melted by a heater, wherein the single crystal occupied by N region over an entire plane in a radial direction is produced with setting an inside diameter of the heater to be 1.26 or more times longer than an inside diameter of the crucible, and an apparatus for producing a single crystal by Czochralski method, at least, comprising a crucible for containing raw material melt, a heater surrounding the crucible so as to heat and melt the raw material melt in the crucible, and a pulling means for pulling the single crystal from the raw material melt in the crucible, wherein an inside diameter of the heater is 1.26 or more times longer than an inside diameter of the crucible. There is provided a method and an apparatus for producing a single crystal in which a pulling rate of producing a low-oxygen crystal occupied by N region can be increased, thereby productivity can be improved.